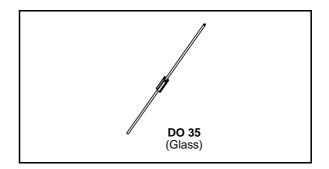


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching.

This device has integrated protection against excessive voltage such as electrostatic discharges.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage	100	V	
l _F	Forward Continuous Current*	100	mA	
I _{FRM}	Repetitive Peak Forward Current*	350	mA	
I_{FSM}	Surge non Repetitive Forward Current* $t_p \le 10 ms$		750	mA
P _{tot}	Power Dissipation*	100	mW	
$T_{stg} \ T_{j}$	Storage and Junction Temperature Range	- 65 to +150 - 65 to +125	°C °C	
T_L	Maximum Lead Temperature for Soldering d from Case	230	°C	

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-a)}	Junction-ambient*	300	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions			Тур.	Max.	Unit
V_{BR}	$T_j = 25^{\circ}C$ $I_R = 100\mu A$		100			V
V _F * *	$T_j = 25^{\circ}C$ $I_F = 1mA$			0.4	0.45	V
	$T_j = 25^{\circ}C$ $I_F = 200mA$				1	
I _R * *	$T_j = 25^{\circ}C$ V_R	2 = 50V			0.1	μΑ
	$T_j = 100^{\circ}C$				20	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _j = 25°C	$V_R = 1V$	f = 1MHz		2		pF

^{*} On infinite heatsink with 4mm lead length * * Pulse test: $t_p \! \leq \! 300 \mu s \; \; \delta \! < \! 2\%$.

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Figure 1. Forward current versus forward voltage at different temperatures (typical values).

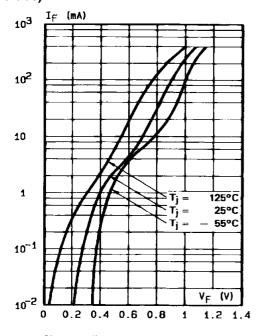


Figure 2. Forward current versus forward voltage (typical values).

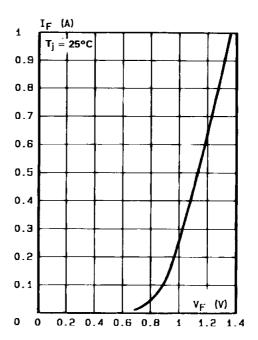


Figure 3. Reverse current versus junction temperature.

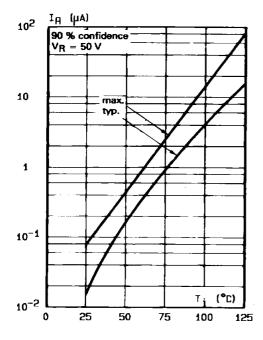


Figure 4. Reverse current versus continuous reverse voltage (typical values).

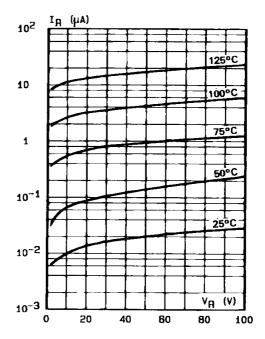
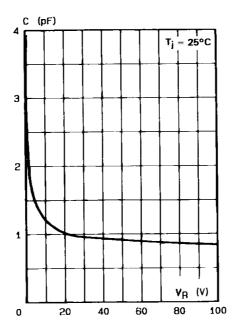
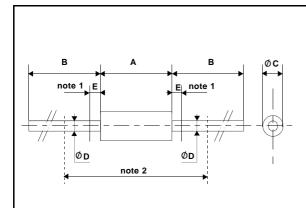


Figure 5. Capacitance C versus reverse applied voltage $V_{\mbox{\scriptsize R}}$ (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



	DIMENSIONS					
REF.	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	3.05	4.50	0.120	0.177		
В	1.53	2.00	0.060	0.079		
С	12.7		0.500			
D	0.458	0.558	0.018	0.022		

Cooling method: by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

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